

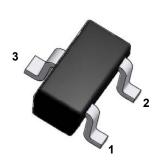
SOT-523 General Purpose Transistor NPN Silicon Surface Mount Plastic Package

Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current	200	mA
P _D	Power Dissipation (FR-4 Board – minimum pad)	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	600	°C /W
T _J T _{STG}	Junction & Storage Temperature Range	-55 to +150	°C

These ratings are limiting values above which the serviceability of the device may be impaired.

Green Product



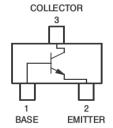
SOT-523 (SC-75A)

Specification Features:

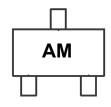
Simplifies Circuit Design

- **RoHS Compliant**
- Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:







Electrical Characteristics (T_A = 25°C unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Condition	Limits		Unit
	Farameter	rest Condition	Min	Max	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (Note 1)	I _C =1mA, I _B =0A	40	-	Volts
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C =10uA, I _E =0A	60	-	Volts
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E =10uA, I _B =0A	6	-	Volts
I _{BL}	Base Cutoff Current	V _{CE} =30V, V _{EB} =3V	-	50	nA
I _{CEX}	Collector Cutoff Current	V _{CE} =30V, V _{EB} =3V	-	50	nA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%)

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On Characteristics (Note 1)

Symbol	Parameter	Test Condition	Limits		Unit
	Farameter	rest Condition	Min	Max	
H _{FE}	DC Current Dain	I _C =0.1mA, V _{CE} =1V	40	-	
		$I_C = 1.0 \text{mA}, V_{CE} = 1 \text{V}$	70	-	
		I_C =10mA, V_{CE} =1V	100	300	-
		I_C =50mA, V_{CE} =1V	60	-	
		I _C =100mA, V _{CE} =1V	30	-	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =1mA	-	0.2	Volts
		I _C =50mA, I _B =5mA	-	0.3	VOILS
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C =10mA, I _B =1mA	0.65	0.85	Volts
		I _C =50mA, I _B =5mA	-	0.95	VOILS

Small-signal Characteristics

Symbol	Parameter	Test Condition	Limits		Unit
Symbol	Parameter	rest Condition	Min	Max	
f _T	Current-Gain-Bandwidth Product	I _C =10mA, V _{CE} =20V, f = 100MHz	200	-	MHz
C _{obo}	Output Capacitance	V _{CB} =5V, I _E =0A, f = 1.0MHz	-	4	pF
C _{ibo}	Input Capacitance	V _{BE} =0.5V, I _C =0A, f = 1.0MHz	-	8	pF
h _{ie}	Input Impedancen	V _{CE} =10V, I _C =1mA, f = 1.0kHz	1	10	pF
h _{re}	Voltage Feedback Ratio	V _{CE} =10V, I _C =1mA, f = 1.0kHz	0.5	8	X10 ⁻⁴
h _{fe}	Small-signal Current Gain	V _{CE} =10V, I _C =1mA, f = 1.0kHz	100	400	-
h _{oe}	Output Admittance	V _{CE} =10V, I _C =1mA, f = 1.0kHz	1	40	θ mhos
NF	Noise Figure	V _{CE} =5V, I _C =100uA		5	dB
		Rs=1.0k Ω f = 1.0kHz			

Switching Characteristics

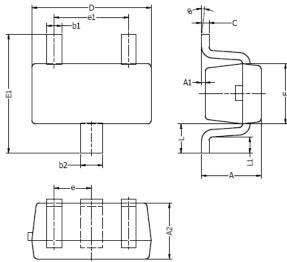
Cumbal	Davamatav	Toot Condition	Limits		l lmi4	
Symbol	Parameter	Test Condition	Min	Max	Unit	
t d	Delay Time	$V_{CC} = 3V$, $V_{BE} = 0.5V$,	-	35	nS	
\mathbf{t}_{r}	Rise Time	I _C =10mA, I _{B1} =1mA	-	35	113	
t s	Storage Time	V _{CC} =3V, I _C =10mA,	-	200	nS	
\mathbf{t}_{f}	Fall Time	$I_{B1} = I_{B2} = 1mA$	-	50	110	

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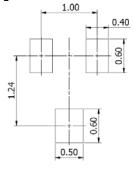


SOT-523 Package Outline



-	_	Ţ	- A	-
-e		A2		

Typical Soldering Pattern:



MILLIMETERS INCHES				
DIM	WILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
С	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
е	0.50	0.50 TYP. 0.020 TYP.		TYP.
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016	REF.
L1	0.10	0.30	0.004	0.012
θ	O °	8 °	O °	8 °
OTEC:				

NOTES:

- 1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
- 2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.





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